

# AXIAL LEADED SILICON RECTIFIER DIODES

## VOLTAGE RANGE: 1000V CURRENT: 1.0 A

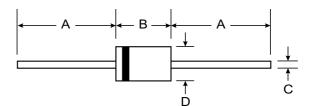
### Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

### **Mechanical Data**

- Case: DO-15
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.40 grams (approx.)
- Mounting Position: Any
- Marking: Type Number





DO-15			
Dim	Min	Max	
Α	25.40	—	
В	5.50	7.62	
С	0.686	0.889	
D	2.60	3.60	
All Dimensions in mm			

#### Maximum Ratings and Electrical Characteristics T<sub>A</sub> = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	SYMBOL	1S1830	UNIT
Maximum Recurrent Peak Reverse Voltage	Vrrm	1000	V
Maximum Average Forward Current 0.375"(9.5mm) Lead Length Ta = 50 °C	lF(AV)	1.0	A
Peak Forward Surge Current, 8.3ms Single half sine wave Superimposed on rated load (JEDEC Method)	IFSM	45	A
Maximum Peak Forward Voltage at IF = 1.5 Amps.	VF	1.2	V
Repetitive Peak Reverse	I <sub>RRM(1)</sub>	10	μA
Current Tj = 150 °C	IRRM(2)	400	μΑ
Storage Temperature Range	Tstg	- 40 to + 150	С
Junction Temperature Range	TJ	- 40 to + 150	°C
Thermal Resistance (Junction to Ambient) DC	Rth(j-a)	100	°C/W

#### Notes :

(1) Reverse Recovery Test Conditions : IF = 0.5 A, IR = 1.0 A, Irr = 0.25 A.

(2) Measured at 1.0 MHz and applied reverse voltage of 4.0  $V_{\text{DC}}$ 



